

*陳乃權教授

所有發表期刊論文

1. J.F. Chen, **N.C. Chen**, S.Y. Chiu, P.Y. Wang, W.I. Lee and A. Chin, "Temperature-dependent transport properties of n+ GaAs/low-temperature GaAs/n+ GaAs structures grown by molecular beam epitaxy", J. Appl. Phys. 79, 8488 (1996).
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